

Form PTO-1449
(Rev. 8-83)

U.S. Department of Commerce
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Attorney Docket No. 0756-2149

Serial No. Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Hisashi OHTANI et al.

Filing Date: June 14, 2000

Group: 2824

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
CN	3,856,565	12/24/74	Arnold			
CN	5,248,630	09/28/93	Serikawa et al			
CN	5,252,502	10/12/93	Havemann			
CN	5,395,804	03/07/95	Ueda			
CN	5,550,070	8/27/96	Funai et al.			
CN	5,147,826	9/15/92	Liu et al.			
CN	5,275,851	1/4/94	Fonash			
CN	5,075,259	12/24/91	Moran			
CN	5,488,000	1/30/96	Zhang et al.			
CN	5,403,772	4/4/95	Zhang et al.			

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	Document Number	Date	Country	Class	Subclass	Translation Yes No
	3-25540	01/30/91	Japan			Abstract
CN	3-280420	12/11/91	Japan			Full

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

CN		Wolf, Stanley, "Silicon Processing for the VLSI Era Volume 2; Process Integration", Lattice Press, 1990, pages 256-257.
CN		Wolf et al., "Silicon Processing for the VLSI Era Volume 1; Process Technology", Lattice Press, 1986, pages 215-216.
CN		C. Hayzelden et al., "In Situ Transmission Electron Microscopy Studies of Silicide-Mediated Crystallization of Amorphous Silicon", 1991.
CN		A.V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals", <u>Akademikian Lavrentev Prospekt</u> 13, 630090 Novosibirsk 90, USSR, pp. 635-640, 1986.
CN		T. Hempel et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films", <u>Solid State Communications</u> , Vol. 85, No. 11, pp. 921-924, 1993.
CN		R. Kakkad, J. Smith, W.S. Lau, S.J. Fonash, "Crystallized Si Films By Low-Temperature Rapid Thermal Annealing of Amorphous Silicon", <u>J. Appl. Phys.</u> 65 (5), March 1, 1989, 1989 American Institute of Physics, pp. 2069-2072.

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cn	5,481,121	01/02/96	Zhang et al			
cn	5,488,000	01/30/96	Zhang et al			
cn	5,492,843	02/20/96	Adachi et al			
cn	5,501,989	03/26/96	Takayama et al			
cn	5,508,533	04/16/96	Takemura			
cn	5,529,937	06/25/96	Zhang et al			
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cn	5,563,426	10/08/96	Zhang et al			
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cn	5,616,506	04/01/97	Takemura			

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cn	5,656,825	08/12/97	Kusumoto et al			
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cn	5,756,364	05/26/98	Tanaka et al			

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cn	G. Liu and S.J. Fonash, "Selective Area Crystallization of Amorphous Silicon Films by Low-Temperature Rapid Thermal Annealing", Appl. Phys. Lett. 55 (7), August 14, 1989, 1989 American Institute of Physics, pp. 660-662.
cn	R. Kakkad, G. Liu, S.J. Fonash, "Low Temperature Selective Crystallization of Amorphous Silicon", Journal of Non-Crystalline Solids, Volume 115, (1989), pp. 66-68.

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cn	5,244,836	09/14/93	Lim	437	192	
cn	3,783,049	01/01/74	Sandera	437	159	
cn	4,959,247	09/25/90	Moser et al.	427	126.5	
cn	5,358,907	10/25/94	Wong	437	230	
cn	5,480,811	01/02/96	Chiang et al.	437	159	
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cn	5,529,937	06/25/96	Zhang et al.			

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	Y. Kawazu et al., Jpn. J. Appl. Phys. 29(4) (1990) 729-738, "Initial Stage of the Interfacial Reaction Between Nickel and Hydrogenated Amorphous Silicon."
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	T.B. Suresh et al., Thin Solid Films, 252 (1994) 78-81 "Electroless Plated Nickel Contacts to Hydrogenated Amorphous Silicon"
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						Yes	No
cn	3-22540	01/30/1991	Japan			Full	

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